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High voltage, high current Darlington transistor array

BA12001B / BA12003B / BA12003BF / BA12004B

The BA12001B, BA12003B, BA12003BF, and BA12004B are high voltage, high current, high sustain voltage transistor arrays consisting of seven circuits of Darlington transistors.

Because it incorporates built-in surge-absorbing diodes and base current-control resistors needed when using inductive loads such as relay coils, attachments can be kept to a minimum.

With an output sustain voltage as high as 60V and an output current (sink current) of 500mA, this product is ideal for use with various drivers and as an interface with other elements.

Applications

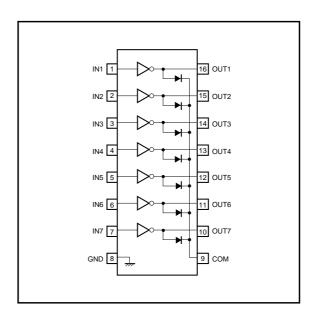
Drivers for LEDs, lamps, relays and solenoids Interface with other elements

Features

- 1) High output current. (IOUT=500mA Max.)
- 2) High output sustain voltage. (VouT=50V Max.)
- 3) Seven Darlington transistors built in.
- 4) Built-in surge-absorbing clamp diode.

(Note: Refer to the "Reference items when using in application.")

Block diagram



•Internal circuit configuration

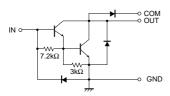


Fig.1 BA12001B

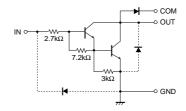


Fig.2 BA12003B / BF

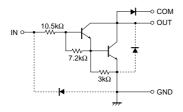


Fig.3 BA12004B

● Absolute maximum ratings (Ta=25°C)

Pa	arameter	Symbol	Limits	Unit	
Power supply voltage		Vce	60	V	
Input voltage	other than BA12001B	Vin -0.5~+30		V	
Input current	BA12001B	lin	25	mA / unit	
Output current		Іоит	500	mA / unit	
Ground pin current		Ignd	2.3*1	Α	
Power dissipation	DIP package	Pd	1250*²	mW	
	SOP package	Pu	625* ³		
Diode reverse voltage		VR	60	V	
Diode forward current		lF	500	mA	
Operating temperature		Topr	-25~+75	°C	
Storage temperature		Tstg	−55~+150	°C	

^{*1} Pulse width ≤ 20ms, duty cycle ≤ 10%, same current for all 7 circuits

● Recommended operating conditions (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Output current	Іоит	_	_	350	mA	Fig.9, 10
Power supply voltage	Vce	_	_	55	V	_
Input voltage (excluding BA12001B)	Vin	_	_	30	V	_
Input current (BA12001B only)	lin	_	-	25	mA / unit	_

^{*2} Reduced by 10mW for each increase in Ta of 1°C over 25°C .

^{*3} Reduced by 50mW for each increase in Ta of 1 $^{\circ}\text{C}$ over 25 $^{\circ}\text{C}$.

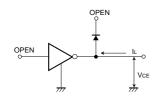
●Electrical characteristics (Ta=25°C)

Parameter		Symbol	Min.	Тур.	Max.	Unit	Conditions
Output leakage current		lι	_	0	10	μΑ	Vce = 60V
DC current transfer ratio		hfe	1000	2400	_	V	VcE = 2V, Iout = 350mA
Output saturation voltage		VCE(sat)	-	0.94	1.1	V	Ιουτ = 100mA, Ιιν = 250μA
				1.14	1.3		Ιουτ = 200mA, Ιιν = 350μA
				1.46	1.6		Ιουτ = 350mA, Ιιν = 500μA
Input voltage	BA12003B / BF	Vin	_	1.75	2	V	
	BA12004B			2.53	5		Vce = 2V, Іоит = 100mA
	BA12003B / BF	Vin	_	1.91	2.4	V	VcE = 2V, IouT = 200mA
	BA12004B			2.75	6		
	BA12003B / BF	.,	_	2.17	3.4	V	VcE = 2V, Iout = 350mA
	BA12004B	Vin		3.27	8		
Input current	BA12003B / BF	lin		0.90	1.35	mA	V _{IN} = 3.85V
	BA12004B		-	0.39	0.5		V _{IN} = 5V
Diode reverse current		lr	_	0	50	μА	V _R = 60V
Diode forward voltage		VF	_	1.73	2	V	I _F = 350mA
Input capacitance		Cin	_	30	-	pF	V _{IN} = 0V, f = 1MHz

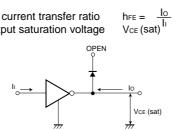
Note: Input voltage and input current for BA12001 vary based on external resistor.

Measurement circuits

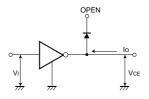
(1) Output leakage current IL



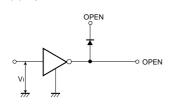
(2) DC current transfer ratio Output saturation voltage



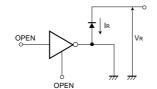
(3) Input voltage VIN



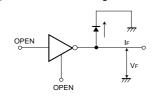
(4) Input current IIN



(5) Diode reverse current IR



(6) Diode forward voltage IF



(7) Input capacitance CIN

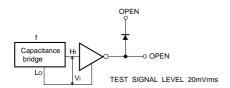


Fig.4

Application example

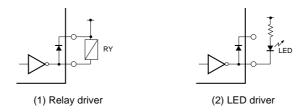


Fig.5

Application notes

The BA12001B is a transistor array which can be directly coupled to a general logic circuit such as PMOS, CMOS, or TTI

A current limiting resistor needs to be connected in series with the input.

The BA12003B / BF can be coupled directly to TTL or CMOS output (when operating at 5V). In order to limit the input current to a stable value, resistors are connected in series to each of the inputs.

The BA12004B is designed for direct coupling to CMOS or PMOS output using a 6 to 15V power supply voltage. In order to limit the input current to a stable value, resistors are connected in series to each of the inputs.

The load for each of these products should be connected between the driver output and the power supply. To protect the IC from excessive swing voltage, the COM pin (Pin 9) should be connected to the power supply.

Fig.6 shows the configuration of the on-chip diode for surge absorption.

In the construction of the surge-absorbing diode, there is an N-P junction between the N-layer (N-well + BL) and the substrate (P-sub) so that when the diode is on, current flows from the output pin to the substrate. In terms of the vertical construction, this diode is configured similar to a PNP transistor. When using the surge-absorbing diode, take appropriate measures regarding the thermal characteristics of the design considering the current that will be handled.

Also, if motor back-rush current or other conditions that will result continued surge current to flow to the surge-absorbing diode can be foreseen, we strongly recommend connecting a Schottky barrier diode (or other type of diode with a low foward voltage) in parallel with the surge-absorbing diode to construct a bypass route for the surge current.

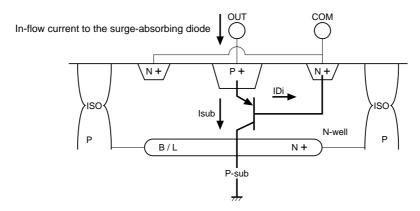


Fig.6 Vertical construction of the surge-absorbing diode

Electrical characteristic curves

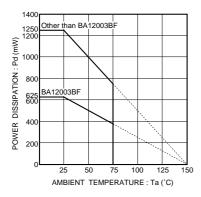


Fig.7 Power dissipation vs. ambient temperature

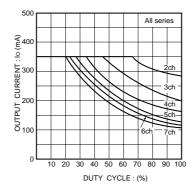


Fig.8 Output conditions (I)

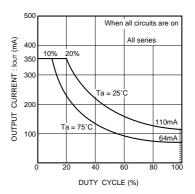


Fig.9 Output conditions (II)

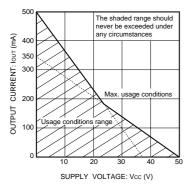


Fig.10 Usage conditions range per circuit

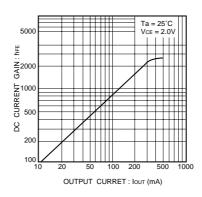


Fig.11 DC current transfer ratio vs. output current

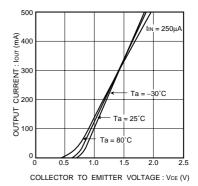


Fig.12 Output current vs. voltage between collector and emitter

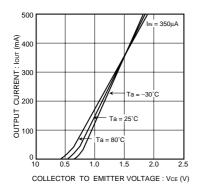


Fig.13 Output current vs. voltage between collector and emitter

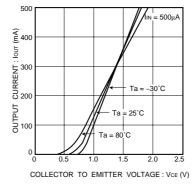


Fig.14 Output current vs. voltage between collector and emitter

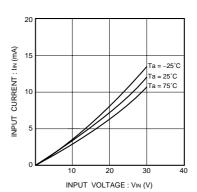


Fig.15 Input current vs. input voltage (BA12003B / BF)

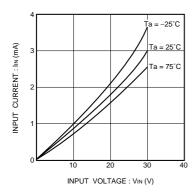


Fig.16 Input current vs. input voltage (BA12004B)

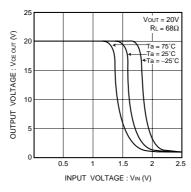


Fig.17 Output voltage vs. input voltage (BA12003B / BF)

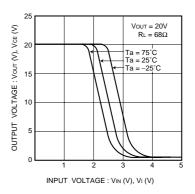
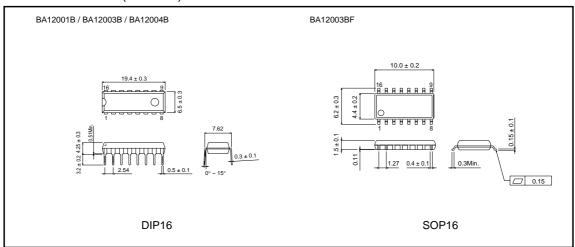


Fig.18 Output voltage vs. input voltage (BA12004B)

●External dimensions (Units : mm)



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